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REVISION HISTORY

7/2019—Rev. C to Rev. D

Changes to CQC Parameter, Table 11	11
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9/2017—Rev. B to Rev. C

Changes to Ordering Guide	19
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9/2016—Rev. A to Rev. B

Change to General Description Section	1
Changes to Table 11	11

4/2016—Rev. 0 to Rev. A

Changes to Features Section	1
Changes to Jitter Measurement Section	17
Changes to Ordering Guide	19
Added Automotive Products Section	19

1/2016—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION

All typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 5\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range of $4.5\text{ V} \leq V_{DD1} \leq 5.5\text{ V}$, $4.5\text{ V} \leq V_{DD2} \leq 5.5\text{ V}$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching specifications are tested with $C_L = 15\text{ pF}$ and CMOS signal levels, unless otherwise noted. Supply currents are specified with 50% duty cycle signals.

Table 1.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Pulse Width	PW	6.6			ns	Within pulse width distortion (PWD) limit
Data Rate		150			Mbps	Within PWD limit
Propagation Delay	t_{PHL} , t_{PLH}	4.8	7.2	13	ns	50% input to 50% output
Pulse Width Distortion	PWD		0.5	3	ns	$ t_{PLH} - t_{PHL} $
Change vs. Temperature			1.5		ps/ $^\circ\text{C}$	
Propagation Delay Skew	t_{PSK}			6.0	ns	Between any two units at the same temperature, voltage, and load
Channel Matching						
Codirectional	t_{PSKCD}		0.5	3.0	ns	
Opposing Direction	t_{PSKOD}		0.5	3.0	ns	
Jitter			380		ps p-p	See the Jitter Measurement section
			55		ps rms	See the Jitter Measurement section
DC SPECIFICATIONS						
Input Threshold Voltage						
Logic High	V_{IH}	$0.7 \times V_{DDx}$			V	
Logic Low	V_{IL}			$0.3 \times V_{DDx}$	V	
Output Voltage						
Logic High	V_{OH}	$V_{DDx} - 0.1$	V_{DDx}		V	$I_{Ox}^1 = -20\text{ }\mu\text{A}$, $V_{Ix} = V_{IxH}^2$
		$V_{DDx} - 0.4$	$V_{DDx} - 0.2$		V	$I_{Ox}^1 = -4\text{ mA}$, $V_{Ix} = V_{IxH}^2$
Logic Low	V_{OL}		0.0	0.1	V	$I_{Ox}^1 = 20\text{ }\mu\text{A}$, $V_{Ix} = V_{IxL}^3$
			0.2	0.4	V	$I_{Ox}^1 = 4\text{ mA}$, $V_{Ix} = V_{IxL}^3$
Input Current per Channel	I_i	-10	+0.01	+10	μA	$0\text{ V} \leq V_{Ix} \leq V_{DDx}$
Quiescent Supply Current						
ADuM120N						
$I_{DD1}(Q)$			0.9	1.3	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD2}(Q)$			1.3	1.8	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD1}(Q)$			6.4	10.0	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
$I_{DD2}(Q)$			1.4	1.9	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
ADuM121N						
$I_{DD1}(Q)$			1.1	1.6	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD2}(Q)$			1.1	1.5	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD1}(Q)$			4.0	5.8	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
$I_{DD2}(Q)$			4.9	6.4	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
Dynamic Supply Current						
Dynamic Input	$I_{DDI}(D)$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Dynamic Output	$I_{DDO}(D)$		0.02		mA/Mbps	Inputs switching, 50% duty cycle
Undervoltage Lockout	UVLO					
Positive V_{DDx} Threshold	V_{DDxUV+}		1.6		V	
Negative V_{DDx} Threshold	V_{DDxUV-}		1.5		V	
V_{DDx} Hysteresis	V_{DDxUVH}		0.1		V	

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
AC SPECIFICATIONS						
Output Rise/Fall Time	t_R/t_F		2.5		ns	10% to 90%
Common-Mode Transient Immunity ⁶	$ CM_H $	75	100		kV/ μ s	$V_{IX} = V_{DDX}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
	$ CM_L $	75	100		kV/ μ s	$V_{IX} = 0$ V, $V_{CM} = 1000$ V, transient magnitude = 800 V

¹ I_{OX} is the Channel x output current, where x = A or B.

² V_{IH} is the input side logic high voltage.

³ V_{IL} is the input side logic low voltage.

⁴ V_I is the input voltage.

⁵ N0 is the ADuM120N0/ADuM121N0 models, and N1 is the ADuM120N1/ADuM121N1 models. See the Ordering Guide.

⁶ $|CM_H|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining the voltage output (V_O) > 0.8 V_{DDX} . $|CM_L|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8$ V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

Table 2. Total Supply Current vs. Data Throughput

Parameter	Symbol	1 Mbps			25 Mbps			100 Mbps			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SUPPLY CURRENT											
ADuM120N											
Supply Current Side 1	I _{DD1}		3.7	6.8		4.2	7.2		6.2	9.3	mA
Supply Current Side 2	I _{DD2}		1.4	2.0		2.5	3.2		6.0	8.1	mA
ADuM121N											
Supply Current Side 1	I _{DD1}		2.6	4.5		3.2	5.4		5.4	8.2	mA
Supply Current Side 2	I _{DD2}		3.0	4.9		3.7	5.9		5.8	8.6	mA

ELECTRICAL CHARACTERISTICS—3.3 V OPERATION

All typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 3.3\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range: $3.0\text{ V} \leq V_{DD1} \leq 3.6\text{ V}$, $3.0\text{ V} \leq V_{DD2} \leq 3.6\text{ V}$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching specifications are tested with $C_L = 15\text{ pF}$ and CMOS signal levels, unless otherwise noted. Supply currents are specified with 50% duty cycle signals.

Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Pulse Width	PW	6.6			ns	Within PWD limit
Data Rate		150			Mbps	Within PWD limit
Propagation Delay	t_{PHL}, t_{PLH}	4.8	6.8	14	ns	50% input to 50% output
Pulse Width Distortion	PWD		0.7	3	ns	$ t_{PLH} - t_{PHL} $
Change vs. Temperature			1.5		ps/ $^\circ\text{C}$	
Propagation Delay Skew	t_{PSK}			7.0	ns	Between any two units at the same temperature, voltage, and load
Channel Matching						
Codirectional	t_{PSKCD}		0.7	3.0	ns	
Opposing Direction	t_{PSKOD}		0.7	3.0	ns	
Jitter			290		ps p-p	See the Jitter Measurement section
			45		ps rms	See the Jitter Measurement section
DC SPECIFICATIONS						
Input Threshold Voltage						
Logic High	V_{IH}	$0.7 \times V_{DDx}$			V	
Logic Low	V_{IL}			$0.3 \times V_{DDx}$	V	
Output Voltage						
Logic High	V_{OH}	$V_{DDx} - 0.1$	V_{DDx}		V	$I_{OX}^1 = -20\text{ }\mu\text{A}$, $V_{IX} = V_{IXH}^2$
		$V_{DDx} - 0.4$	$V_{DDx} - 0.2$		V	$I_{OX}^1 = -2\text{ mA}$, $V_{IX} = V_{IXH}^2$
Logic Low	V_{OL}		0.0	0.1	V	$I_{OX}^1 = 20\text{ }\mu\text{A}$, $V_{IX} = V_{IXL}^3$
			0.2	0.4	V	$I_{OX}^1 = 2\text{ mA}$, $V_{IX} = V_{IXL}^3$
Input Current per Channel	I_I	-10	+0.01	+10	μA	$0\text{ V} \leq V_{IX} \leq V_{DDx}$
Quiescent Supply Current						
ADuM120N						
$I_{DD1(Q)}$			0.8	1.3	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD2(Q)}$			1.2	1.8	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD1(Q)}$			6.3	9.7	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
$I_{DD2(Q)}$			1.3	1.8	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
ADuM121N						
$I_{DD1(Q)}$			1.0	1.6	mA	$V_I^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD2(Q)}$			1.0	1.5	mA	$V_I^4 = 01\text{ (N0)}, 1\text{ (N1)}^5$
$I_{DD1(Q)}$			3.9	5.8	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
$I_{DD2(Q)}$			4.8	6.4	mA	$V_I^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
Dynamic Supply Current						
Dynamic Input	$I_{DDI(D)}$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Dynamic Output	$I_{DDO(D)}$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Undervoltage Lockout	UVLO					
Positive V_{DDx} Threshold	V_{DDxUV+}		1.6		V	
Negative V_{DDx} Threshold	V_{DDxUV-}		1.5		V	
V_{DDx} Hysteresis	V_{DDxUVH}		0.1		V	

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
AC SPECIFICATIONS						
Output Rise/Fall Time	t_R/t_F		2.5		ns	10% to 90%
Common-Mode Transient Immunity ⁶	$ CM_H $	75	100		kV/ μ s	$V_{IX} = V_{DDX}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
	$ CM_L $	75	100		kV/ μ s	$V_{IX} = 0$ V, $V_{CM} = 1000$ V, transient magnitude = 800 V

¹ I_{OX} is the Channel x output current, where x = A or B.

² V_{IH} is the input side logic high voltage.

³ V_{IL} is the input side logic low voltage.

⁴ V_I is the input voltage.

⁵ N0 is the ADuM120N0/ADuM121N0 models, and N1 is the ADuM120N1/ADuM121N1 models. See the Ordering Guide.

⁶ $|CM_H|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8 V_{DDX}$. $|CM_L|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8$ V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

Table 4. Total Supply Current vs. Data Throughput

Parameter	Symbol	1 Mbps			25 Mbps			100 Mbps			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SUPPLY CURRENT											
ADuM120N											
Supply Current Side 1	I _{DD1}		3.6	6.2		4.0	6.7		5.6	9.1	mA
Supply Current Side 2	I _{DD2}		1.3	1.9		2.3	3.1		5.2	6.8	mA
ADuM121N											
Supply Current Side 1	I _{DD1}		2.5	4.6		3.0	5.5		5.0	8.1	mA
Supply Current Side 2	I _{DD2}		2.9	4.8		3.5	5.8		5.4	8.3	mA

ELECTRICAL CHARACTERISTICS—2.5 V OPERATION

All typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 2.5\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range: $2.25\text{ V} \leq V_{DD1} \leq 2.75\text{ V}$, $2.25\text{ V} \leq V_{DD2} \leq 2.75\text{ V}$, $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching specifications are tested with $C_L = 15\text{ pF}$ and CMOS signal levels, unless otherwise noted. Supply currents are specified with 50% duty cycle signals.

Table 5.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Pulse Width	PW	6.6			ns	Within PWD limit
Data Rate		150			Mbps	Within PWD limit
Propagation Delay	t_{PHL} , t_{PLH}	5.0	7.0	14	ns	50% input to 50% output
Pulse Width Distortion	PWD		0.7	3	ns	$ t_{PLH} - t_{PHL} $
Change vs. Temperature			1.5		ps/ $^\circ\text{C}$	
Propagation Delay Skew	t_{PSK}			7.0	ns	Between any two units at the same temperature, voltage, load
Channel Matching						
Codirectional	t_{PSKCD}		0.7	3.0	ns	
Opposing Direction	t_{PSKOD}		0.7	3.0	ns	
Jitter			320		ps p-p	See the Jitter Measurement section
			65		ps rms	See the Jitter Measurement section
DC SPECIFICATIONS						
Input Threshold Voltage						
Logic High	V_{IH}	$0.7 \times V_{DDx}$			V	
Logic Low	V_{IL}			$0.3 \times V_{DDx}$	V	
Output Voltage						
Logic High	V_{OH}	$V_{DDx} - 0.1$	V_{DDx}		V	$I_{Ox}^1 = -20\text{ }\mu\text{A}$, $V_{Ix} = V_{IxH}^2$
		$V_{DDx} - 0.4$	$V_{DDx} - 0.2$		V	$I_{Ox}^1 = -2\text{ mA}$, $V_{Ix} = V_{IxH}^2$
Logic Low	V_{OL}		0.0	0.1	V	$I_{Ox}^1 = 20\text{ }\mu\text{A}$, $V_{Ix} = V_{IxL}^3$
			0.2	0.4	V	$I_{Ox}^1 = 2\text{ mA}$, $V_{Ix} = V_{IxL}^3$
Input Current per Channel	I_I	-10	+0.01	+10	μA	$0\text{ V} \leq V_{Ix} \leq V_{DDx}$
Quiescent Supply Current						
ADuM120N						
$I_{DD1} (Q)$			0.8	1.2	mA	$V_I^4 = 0 (N0)$, 1 (N1) ⁵
$I_{DD2} (Q)$			1.2	1.8	mA	$V_I^4 = 0 (N0)$, 1 (N1) ⁵
$I_{DD1} (Q)$			6.2	9.5	mA	$V_I^4 = 1 (N0)$, 0 (N1) ⁵
$I_{DD2} (Q)$			1.3	1.8	mA	$V_I^4 = 1 (N0)$, 0 (N1) ⁵
ADuM121N						
$I_{DD1} (Q)$			1.0	1.5	mA	$V_I^4 = 0 (N0)$, 1 (N1) ⁵
$I_{DD2} (Q)$			1.0	1.4	mA	$V_I^4 = 0 (N0)$, 1 (N1) ⁵
$I_{DD1} (Q)$			3.9	5.8	mA	$V_I^4 = 1 (N0)$, 0 (N1) ⁵
$I_{DD2} (Q)$			4.8	6.4	mA	$V_I^4 = 1 (N0)$, 0 (N1) ⁵
Dynamic Supply Current						
Dynamic Input	$I_{DDI} (D)$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Dynamic Output	$I_{DDO} (D)$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Undervoltage Lockout						
Positive V_{DDx} Threshold	V_{DDxUV+}		1.6		V	
Negative V_{DDx} Threshold	V_{DDxUV-}		1.5		V	
V_{DDx} Hysteresis	V_{DDxUVH}		0.1		V	

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
AC SPECIFICATIONS						
Output Rise/Fall Time	t_R/t_F		2.5		ns	10% to 90%
Common-Mode Transient Immunity ⁶	$ CM_H $	75	100		kV/ μ s	$V_{IX} = V_{DDX}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
	$ CM_L $	75	100		kV/ μ s	$V_{IX} = 0$ V, $V_{CM} = 1000$ V, transient magnitude = 800 V

¹ I_{OX} is the Channel x output current, where x = A or B.

² V_{IH} is the input side logic high voltage.

³ V_{IL} is the input side logic low voltage.

⁴ V_I is the input voltage.

⁵ N0 is the ADuM120N0/ADuM121N0 models, and N1 is the ADuM120N1/ADuM121N1 models. See the Ordering Guide.

⁶ $|CM_H|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8 V_{DDX}$. $|CM_L|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8$ V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

Table 6. Total Supply Current vs. Data Throughput

Parameter	Symbol	1 Mbps			25 Mbps			100 Mbps			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SUPPLY CURRENT											
ADuM120N											
Supply Current Side 1	I _{DD1}		3.5	6.2		3.9	6.6		5.4	9.0	mA
Supply Current Side 2	I _{DD2}		1.3	1.9		2.0	2.8		4.2	5.8	mA
ADuM121N											
Supply Current Side 1	I _{DD1}		2.4	4.7		2.9	5.5		4.5	8.0	mA
Supply Current Side 2	I _{DD2}		2.9	4.9		3.3	5.7		4.9	7.7	mA

ELECTRICAL CHARACTERISTICS—1.8 V OPERATION

All typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 1.8\text{ V}$. Minimum/maximum specifications apply over the entire recommended operation range: $1.7\text{ V} \leq V_{DD1} \leq 1.9\text{ V}$, $1.7\text{ V} \leq V_{DD2} \leq 1.9\text{ V}$, and $-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise noted. Switching specifications are tested with $C_L = 15\text{ pF}$ and CMOS signal levels, unless otherwise noted. Supply currents are specified with 50% duty cycle signals.

Table 7.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
Pulse Width	PW	6.6			ns	Within PWD limit
Data Rate		150			Mbps	Within PWD limit
Propagation Delay	$t_{\text{PHL}}, t_{\text{PLH}}$	5.8	8.7	15	ns	50% input to 50% output
Pulse Width Distortion	PWD		0.7	3	ns	$ t_{\text{PLH}} - t_{\text{PHL}} $
Change vs. Temperature			1.5		ps/ $^\circ\text{C}$	
Propagation Delay Skew	t_{PSK}			7.0	ns	Between any two units at the same temperature, voltage, and load
Channel Matching						
Codirectional	t_{PSKCD}		0.7	3.0	ns	
Opposing Direction	t_{PSKOD}		0.7	3.0	ns	
Jitter			630		ps p-p	See the Jitter Measurement section
			190		ps rms	See the Jitter Measurement section
DC SPECIFICATIONS						
Input Threshold Voltage						
Logic High	V_{IH}	$0.7 \times V_{\text{DDx}}$			V	
Logic Low	V_{IL}			$0.3 \times V_{\text{DDx}}$	V	
Output Voltage						
Logic High	V_{OH}	$V_{\text{DDx}} - 0.1$	V_{DDx}		V	$I_{\text{Ox}}^1 = -20\text{ }\mu\text{A}$, $V_{\text{Ix}} = V_{\text{IxH}}^2$
		$V_{\text{DDx}} - 0.4$	$V_{\text{DDx}} - 0.2$		V	$I_{\text{Ox}}^1 = -2\text{ mA}$, $V_{\text{Ix}} = V_{\text{IxH}}^2$
Logic Low	V_{OL}		0.0	0.1	V	$I_{\text{Ox}}^1 = 20\text{ }\mu\text{A}$, $V_{\text{Ix}} = V_{\text{IxL}}^3$
			0.2	0.4	V	$I_{\text{Ox}}^1 = 2\text{ mA}$, $V_{\text{Ix}} = V_{\text{IxL}}^3$
Input Current per Channel	I_{I}	-10	+0.01	+10	μA	$0\text{ V} \leq V_{\text{Ix}} \leq V_{\text{DDx}}$
Quiescent Supply Current						
ADuM120N						
$I_{\text{DD1 (Q)}}$			0.7	1.2	mA	$V_{\text{I}}^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{\text{DD2 (Q)}}$			1.2	1.8	mA	$V_{\text{I}}^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{\text{DD1 (Q)}}$			6.2	9.6	mA	$V_{\text{I}}^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
$I_{\text{DD2 (Q)}}$			1.3	1.8	mA	$V_{\text{I}}^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
ADuM121N						
$I_{\text{DD1 (Q)}}$			1.0	1.5	mA	$V_{\text{I}}^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{\text{DD2 (Q)}}$			1.0	1.4	mA	$V_{\text{I}}^4 = 0\text{ (N0)}, 1\text{ (N1)}^5$
$I_{\text{DD1 (Q)}}$			3.8	5.8	mA	$V_{\text{I}}^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
$I_{\text{DD2 (Q)}}$			4.7	6.4	mA	$V_{\text{I}}^4 = 1\text{ (N0)}, 0\text{ (N1)}^5$
Dynamic Supply Current						
Dynamic Input	$I_{\text{DDI (D)}}$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Dynamic Output	$I_{\text{DDO (D)}}$		0.01		mA/Mbps	Inputs switching, 50% duty cycle
Undervoltage Lockout	UVLO					
Positive V_{DDx} Threshold	$V_{\text{DDxUV+}}$		1.6		V	
Negative V_{DDx} Threshold	$V_{\text{DDxUV-}}$		1.5		V	
V_{DDx} Hysteresis	V_{DDxUVH}		0.1		V	

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
AC SPECIFICATIONS						
Output Rise/Fall Time	t_R/t_F		2.5		ns	10% to 90%
Common-Mode Transient Immunity ⁶	$ CM_H $	75	100		kV/ μ s	$V_{ix} = V_{DDx}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
	$ CM_L $	75	100		kV/ μ s	$V_{ix} = 0$ V, $V_{CM} = 1000$ V, transient magnitude = 800 V

¹ I_{Ox} is the Channel x output current, where x = A or B.

² V_{IH} is the input side logic high voltage.

³ V_{IL} is the input side logic low voltage.

⁴ V_i is the input voltage.

⁵ N0 is the ADuM120N0/ADuM121N0 models, N1 is the ADuM120N1/ADuM121N1 models. See the Ordering Guide.

⁶ $|CM_H|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8 V_{DDx}$. $|CM_L|$ is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8$ V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

Table 8. Total Supply Current vs. Data Throughput

Parameter	Symbol	1 Mbps			25 Mbps			100 Mbps			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
SUPPLY CURRENT											
ADuM120N											
Supply Current Side 1	I _{DD1}		3.4	6.0		3.8	6.4		5.2	8.4	mA
Supply Current Side 2	I _{DD2}		1.2	1.8		1.9	2.8		4.0	5.8	mA
ADuM121N											
Supply Current Side 1	I _{DD1}		2.4	4.7		2.8	5.5		4.4	7.8	mA
Supply Current Side 2	I _{DD2}		2.8	4.8		3.2	5.6		4.8	7.9	mA

INSULATION AND SAFETY RELATED SPECIFICATIONS

For additional information, see www.analog.com/icouplersafety.

Table 9.

Parameter	Symbol	Value	Unit	Test Conditions/Comments
Rated Dielectric Insulation Voltage		3000	V rms	1-minute duration
Minimum External Air Gap (Clearance)	L (I01)	4.0	mm min	Measured from input terminals to output terminals, shortest distance through air
Minimum External Tracking (Creepage)	L (I02)	4.0	mm min	Measured from input terminals to output terminals, shortest distance path along body
Minimum Clearance in the Plane of the Printed Circuit Board (PCB Clearance)	L (PCB)	4.5	mm min	Measured from input terminals to output terminals, shortest distance through air, line of sight, in the PCB mounting plane
Minimum Internal Gap (Internal Clearance)		25.5	μ m min	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	CTI	>400	V	DIN IEC 112/VDE 0303 Part 1
Material Group		II		Material Group (DIN VDE 0110, 1/89, Table 1)

PACKAGE CHARACTERISTICS

Table 10.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
Resistance (Input to Output) ¹	R_{I-O}		10^{13}		Ω	
Capacitance (Input to Output) ¹	C_{I-O}		2		pF	$f = 1$ MHz
Input Capacitance ²	C_i		4.0		pF	
IC Junction to Ambient Thermal Resistance	θ_{JA}		80		$^{\circ}\text{C/W}$	Thermocouple located at center of package underside

¹ The device is considered a 2-terminal device: Pin 1 through Pin 4 are shorted together, and Pin 5 through Pin 8 are shorted together.

² Input capacitance is from any input data pin to ground.

REGULATORY INFORMATION

See Table 15 and the Insulation Lifetime section for details regarding recommended maximum working voltages for specific cross-isolation waveforms and insulation levels.

Table 11.

Regulatory Body	Insulation Parameter	Insulation Specifications	Recognition/Approval Program	File
UL (PENDING)	Single protection	3000 V rms isolation voltage	Recognized under UL 1577 Component Recognition Program ¹	File E214100
CSA (PENDING) CSA 60950-1-07+A1+A2 and IEC 60950-1, Second Edition, +A1+A2 IEC 60601-1 Edition 3.1 CSA 61010-1-12 and IEC 61010-1 Third Edition	Basic insulation Reinforced insulation Basic insulation (1 MOPP) Basic insulation Reinforced insulation	400 V rms (565 V peak) 200 V rms (283 V peak) 250 V rms (354 V peak) 300 V rms mains, 400 V rms (565 V peak) 300 V rms mains, 200 V secondary (283 V peak)	Approved under CSA Component Acceptance Notice	File 205078
VDE (PENDING)	Basic insulation Reinforced insulation	565 V peak, VIOSM = 10,000 V peak 565 V peak, VIOSM = 6000 V peak	DIN V VDE V 0884-10 (VDE V 0884-10):2006-122 ²	File 2471900-4880-0001
CQC GB4943.1-2011	Basic insulation	400 V rms (565 V peak) working voltage	Certified under CQC11-471543-2015	File CQC18001192422

¹ In accordance with UL 1577, each ADuM120N/ADuM121N is proof tested by applying an insulation test voltage ≥ 3600 V rms for 1 sec.

² In accordance with DIN V VDE V 0884-10, each ADuM120N/ADuM121N is proof tested by applying an insulation test voltage ≥ 1059 V peak for 1 sec (partial discharge detection limit = 5 pC). The * marking branded on the component designates DIN V VDE V 0884-10 approval.

DIN V VDE V 0884-10 (VDE V 0884-10) INSULATION CHARACTERISTICS

These isolators are suitable for reinforced electrical isolation only within the safety limit data. Protective circuits ensure the maintenance of the safety data. The * marking on packages denotes DIN V VDE V 0884-10 approval.

Table 12.

Description	Test Conditions/Comments	Symbol	Characteristic	Unit
Installation Classification per DIN VDE 0110 For Rated Mains Voltage ≤ 150 V rms For Rated Mains Voltage ≤ 300 V rms For Rated Mains Voltage ≤ 400 V rms Climatic Classification Pollution Degree per DIN VDE 0110, Table 1 Maximum Working Insulation Voltage Input to Output Test Voltage, Method B1	$V_{IORM} \times 1.875 = V_{pd(m)}$, 100% production test, $t_{ini} = t_m = 1$ sec, partial discharge < 5 pC	V_{IORM} $V_{pd(m)}$	I to IV I to III I to III 40/105/21 2 565 1059	V peak V peak
Input to Output Test Voltage, Method A After Environmental Tests Subgroup 1	$V_{IORM} \times 1.5 = V_{pd(m)}$, $t_{ini} = 60$ sec, $t_m = 10$ sec, partial discharge < 5 pC	$V_{pd(m)}$	848	V peak
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{IORM} \times 1.2 = V_{pd(m)}$, $t_{ini} = 60$ sec, $t_m = 10$ sec, partial discharge < 5 pC		678	V peak
Highest Allowable Overvoltage		V_{IOTM}	4200	V peak
Surge Isolation Voltage Basic	V peak = 10 kV, 1.2 μs rise time, 50 μs, 50% fall time	V_{IOSM}	10000	V peak
Surge Isolation Voltage Reinforced	V peak = 10 kV, 1.2 μs rise time, 50 μs, 50% fall time	V_{IOSM}	6000	V peak
Safety Limiting Values	Maximum value allowed in the event of a failure (see Figure 3)			
Maximum Junction Temperature		T_S	150	°C
Total Power Dissipation at 25°C		P_S	1.56	W
Insulation Resistance at T_S	$V_{IO} = 500$ V	R_S	$>10^9$	Ω

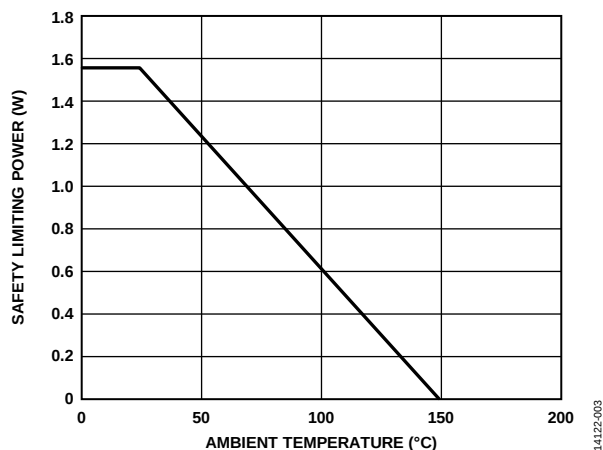


Figure 3. Thermal Derating Curve, Dependence of Safety Limiting Values with Ambient Temperature per DIN V VDE V 0884-10

RECOMMENDED OPERATING CONDITIONS**Table 13.**

Parameter	Symbol	Rating
Operating Temperature	T_A	−40°C to +125°C
Supply Voltages	V_{DD1}, V_{DD2}	1.7 V to 5.5 V
Input Signal Rise and Fall Times		1.0 ms

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 14.

Parameter	Rating
Supply Voltages (V_{DD1} , V_{DD2})	–0.5 V to +7.0 V
Input Voltages (V_{IA} , V_{IB}) ¹	–0.5 V to $V_{DD1} + 0.5$ V
Output Voltages (V_{OA} , V_{OB}) ²	–0.5 V to $V_{DDO} + 0.5$ V
Average Output Current per Pin ³	
Side 1 Output Current (I_{O1})	–10 mA to +10 mA
Side 2 Output Current (I_{O2})	–10 mA to +10 mA
Common-Mode Transients ⁴	–150 kV/ μ s to +150 kV/ μ s
Storage Temperature (T_{ST}) Range	–65°C to +150°C
Ambient Operating Temperature (T_A) Range	–40°C to +125°C

¹ V_{DD1} is the input side supply voltage.

² V_{DDO} is the output side supply voltage.

³ See Figure 3 for the maximum rated current values for various temperatures.

⁴ Common-mode transients refer to the common-mode transients across the insulation barrier. Common-mode transients exceeding the absolute maximum ratings can cause latch-up or permanent damage.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Table 15. Maximum Continuous Working Voltage¹

Parameter	Rating	Constraint ²
AC VOLTAGE		Lifetime limited by package creepage maximum approved working voltage per IEC 60950-1
Bipolar Waveform		
Basic Insulation	789 V peak	
Reinforced Insulation	403 V peak	
Unipolar Waveform		
Basic Insulation	909 V peak	
Reinforced Insulation	469 V peak	
DC VOLTAGE		Lifetime limited by package creepage maximum approved working voltage per IEC 60950-1
Basic Insulation	558 V peak	
Reinforced Insulation	285 V peak	

¹ Maximum continuous working voltage refers to the continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

² Insulation lifetime for the specified test condition is greater than 50 years.

Truth Tables

Table 16. ADuM120N/ADuM121N Truth Table (Positive Logic)

V_{IX} Input ¹	V_{DD1} State ¹	V_{DDO} State ¹	Default Low (N0), V_{OX} Output ^{1,2}	Default High (N1), V_{OX} Output ^{1,2}	Test Conditions/Comments
Low	Powered	Powered	Low	Low	Normal operation
High	Powered	Powered	High	High	Normal operation
Don't Care ³	Unpowered	Powered	Low	High	Fail-safe output
Don't Care ³	Powered	Unpowered	Indeterminate	Indeterminate	

¹ V_{IX} and V_{OX} refer to the input and output signals of a given channel (A or B). V_{DD1} and V_{DDO} refer to the supply voltages on the input and output sides of the given channel, respectively.

² N0 is the ADuM120N0/ADuM121N0 models, N1 is the ADuM120N1/ADuM121N1 models. See the Ordering Guide.

³ Input pins (V_{IX}) on the same side as an unpowered supply must be in a low state to avoid powering the device through the ESD protection circuitry.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

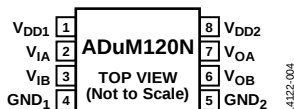


Figure 4. ADuM120N Pin Configuration

Reference the [AN-1109 Application Note](#) for specific layout guidelines.

Table 17. ADuM120N Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1.
2	V _{IA}	Logic Input A.
3	V _{IB}	Logic Input B.
4	GND ₁	Ground 1. This pin is the ground reference for Isolator Side 1.
5	GND ₂	Ground 2. This pin is the ground reference for Isolator Side 2.
6	V _{OB}	Logic Output B.
7	V _{OA}	Logic Output A.
8	V _{DD2}	Supply Voltage for Isolator Side 2.

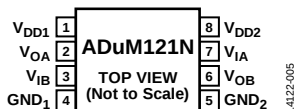


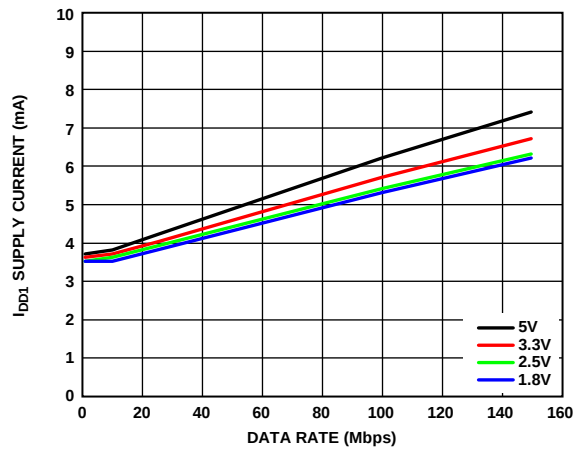
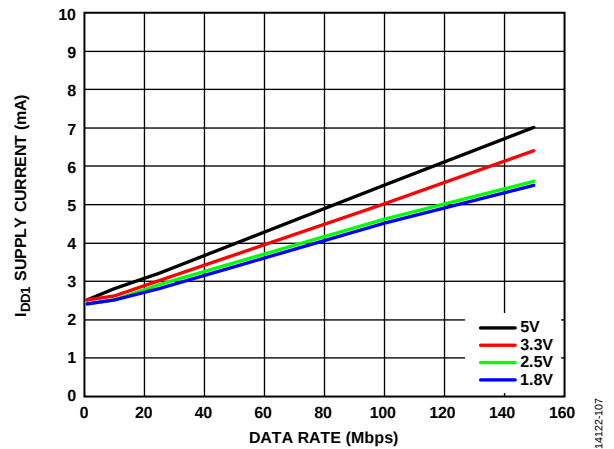
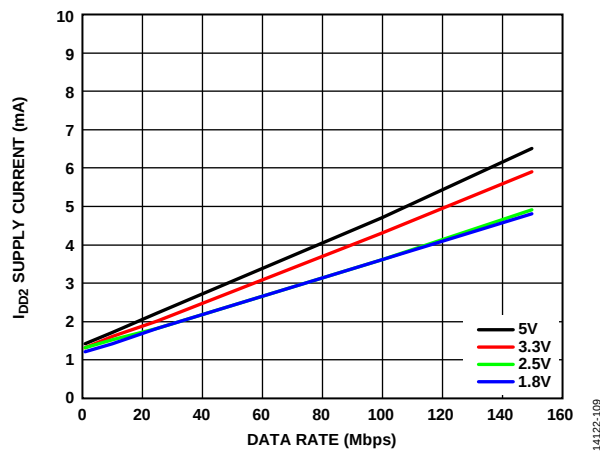
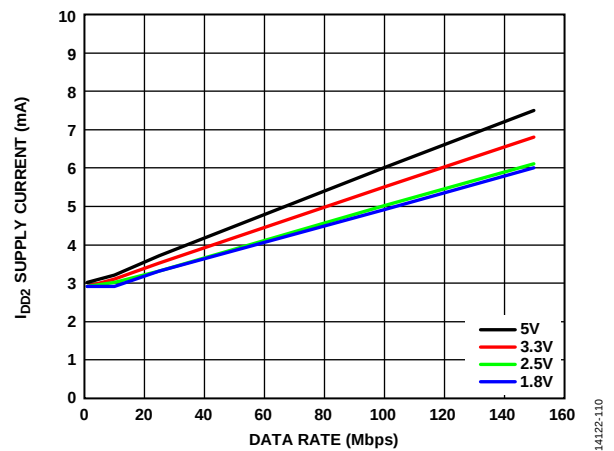
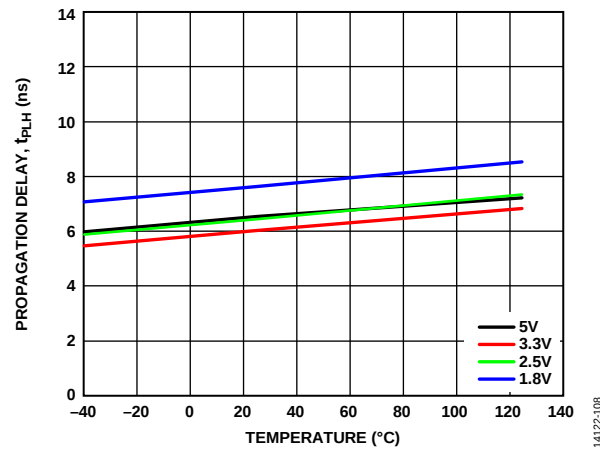
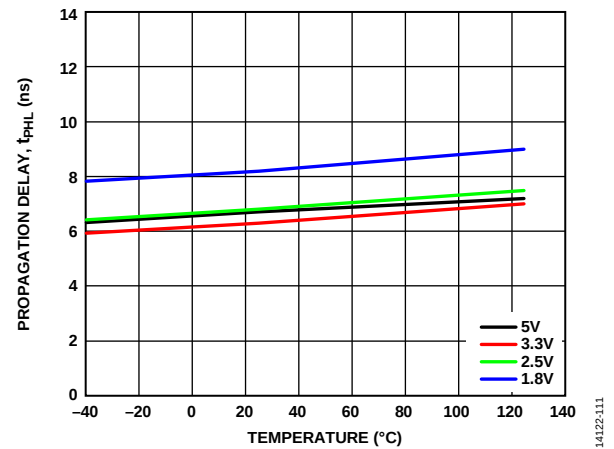
Figure 5. ADuM121N Pin Configuration

Reference the [AN-1109 Application Note](#) for specific layout guidelines.

Table 18. ADuM121N Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1.
2	V _{OA}	Logic Output A.
3	V _{IB}	Logic Input B.
4	GND ₁	Ground 1. This pin is the ground reference for Isolator Side 1.
5	GND ₂	Ground 2. This pin is the ground reference for Isolator Side 2.
6	V _{OB}	Logic Output B.
7	V _{IA}	Logic Input A.
8	V _{DD2}	Supply Voltage for Isolator Side 2.

TYPICAL PERFORMANCE CHARACTERISTICS

Figure 6. ADuM120N I_{DD1} Supply Current vs. Data Rate at Various VoltagesFigure 9. ADuM121N I_{DD1} Supply Current vs. Data Rate at Various VoltagesFigure 7. ADuM120N I_{DD2} Supply Current vs. Data Rate at Various VoltagesFigure 10. ADuM121N I_{DD2} Supply Current vs. Data Rate at Various VoltagesFigure 8. Propagation Delay for Logic High Output (t_{PLH}) vs. Temperature at Various VoltagesFigure 11. Propagation Delay for Logic Low Output (t_{PHL}) vs. Temperature at Various Voltages

APPLICATIONS INFORMATION

OVERVIEW

The ADuM120N/ADuM121N use a high frequency carrier to transmit data across an isolation barrier using iCoupler chip scale transformer coils separated by layers of polyimide isolation. With an on/off keying (OOK) technique and the differential architecture shown in Figure 13 and Figure 14, the ADuM120N/ADuM121N have very low propagation delay and high speed. Internal regulators and input/output design techniques allow logic and supply voltages over a wide range from 1.7 V to 5.5 V, offering voltage translation of 1.8 V, 2.5 V, 3.3 V, and 5 V logic. The architecture is designed for high common-mode transient immunity and high immunity to electrical noise and magnetic interference. Radiated emissions are minimized with a spread spectrum OOK carrier and other techniques.

Figure 13 shows the operation block diagram of a single channel for the ADuM120N0/ADuM121N0 models, which have the condition of the fail-safe output state equal to low, where the carrier waveform is off when the input state is low. If the input side is off or not operating, the fail-safe output state of low (noted by the 0 in the model number) sets the output to low. For the ADuM120N1/ADuM121N1, which have a fail-safe output state of high, Figure 14 shows the conditions where the carrier waveform is off when the input state is high. When the input side is off or not operating, the fail-safe output state of high (noted by the 1 in the model number) sets the output to high. See the Ordering Guide for the model numbers that have the fail-safe output state of low or the fail-safe output state of high.

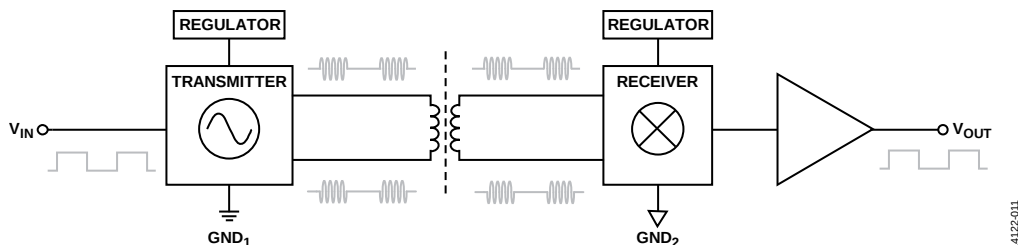


Figure 13. Operational Block Diagram of a Single Channel with a Low Fail-Safe Output State

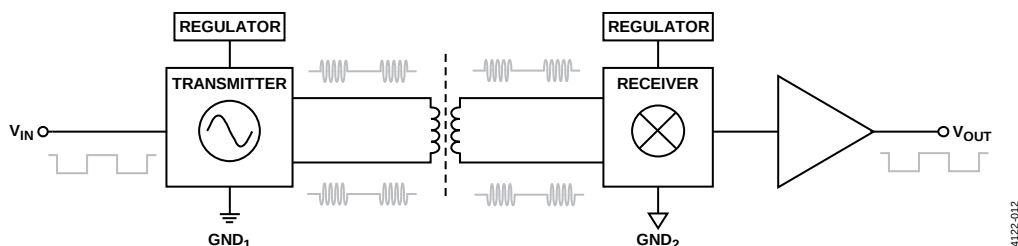


Figure 14. Operational Block Diagram of a Single Channel with a High Fail-Safe Output State

PCB LAYOUT

The ADuM120N/ADuM121N digital isolators require no external interface circuitry for the logic interfaces. Power supply bypassing is strongly recommended at the input and output supply pins (see Figure 12). Bypass capacitors are most conveniently connected between Pin 1 and Pin 4 for V_{DD1} and between Pin 5 and Pin 8 for V_{DD2} . The recommended bypass capacitor value is between 0.01 μ F and 0.1 μ F. The total lead length between both ends of the capacitor and the input power supply pin must not exceed 10 mm.

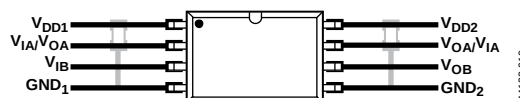


Figure 12. Recommended Printed Circuit Board Layout

In applications involving high common-mode transients, ensure that board coupling across the isolation barrier is minimized. Furthermore, design the board layout such that any coupling that does occur equally affects all pins on a given component side. Failure to ensure this can cause voltage differentials between pins exceeding the Absolute Maximum Ratings of the device, thereby leading to latch-up or permanent damage.

See the AN-1109 Application Note for board layout guidelines.

PROPAGATION DELAY RELATED PARAMETERS

Propagation delay is a parameter that describes the time it takes a logic signal to propagate through a component. The propagation delay to a Logic 0 output can differ from the propagation delay to a Logic 1 output.

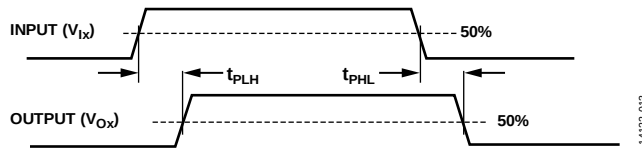


Figure 15. Propagation Delay Parameters

Pulse width distortion is the maximum difference between these two propagation delay values and is an indication of how accurately the timing of the input signal is preserved.

Channel matching is the maximum amount the propagation delay differs between channels within a single ADuM120N/ADuM121N component.

Propagation delay skew is the maximum amount the propagation delay differs between multiple ADuM120N/ADuM121N components operating under the same conditions

JITTER MEASUREMENT

Figure 16 shows the eye diagram for the ADuM120N/ADuM121N. The measurement was taken using an Agilent 81110A pulse pattern generator at 150 Mbps with pseudorandom bit sequences (PRBS) $2(n-1)$, $n=14$, for 5 V supplies. Jitter was measured with the Tektronix Model 5104B oscilloscope, 1 GHz, 10 GS/s with the DPOJET jitter and eye diagram analysis tools. The result shows a typical measurement on the ADuM120N/ADuM121N with 380 ps p-p jitter.

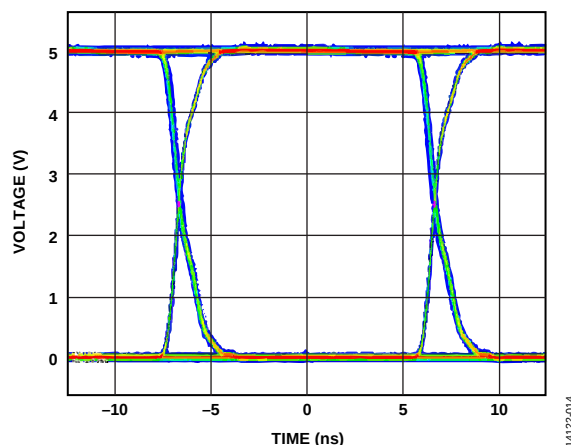


Figure 16. ADuM120N/ADuM121N Eye Diagram

INSULATION LIFETIME

All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation as well as on the materials and material interfaces.

The two types of insulation degradation of primary interest are breakdown along surfaces exposed to the air and insulation wear out. Surface breakdown is the phenomenon of surface tracking and the primary determinant of surface creepage requirements in system level standards. Insulation wear out is the phenomenon where charge injection or displacement currents inside the insulation material cause long-term insulation degradation.

Surface Tracking

Surface tracking is addressed in electrical safety standards by setting a minimum surface creepage based on the working voltage, the environmental conditions, and the properties of the insulation material. Safety agencies perform characterization testing on the surface insulation of components that allows the components to be categorized in different material groups. Lower material group ratings are more resistant to surface tracking and, therefore, can provide adequate lifetime with smaller creepage. The minimum creepage for a given working voltage and material group is in each system level standard and is based on the total rms voltage across the isolation, pollution degree, and material group. The material group and creepage for the ADuM120N/ADuM121N isolators are presented in Table 9.

Insulation Wear Out

The lifetime of insulation caused by wear out is determined by the thickness, material properties, and the voltage stress applied. It is important to verify that the product lifetime is adequate at the application working voltage. The working voltage supported by an isolator for wear out cannot be the same as the working voltage supported for tracking. It is the working voltage applicable to tracking that is specified in most standards.

Testing and modeling show that the primary driver of long-term degradation is displacement current in the polyimide insulation causing incremental damage. The stress on the insulation can be broken down into broad categories, such as dc stress, which causes very little wear out because there is no displacement current, and an ac component time varying voltage stress, which causes wear out.

The ratings in certification documents are usually based on 60 Hz sinusoidal stress because this reflects isolation from line voltage. However, many practical applications have combinations of 60 Hz ac and dc across the barrier as shown in Equation 1. Because only the ac portion of the stress causes wear out, the equation can be rearranged to solve for the ac rms voltage, as is shown in Equation 2. For insulation wear out with the polyimide materials used in these products, the ac rms voltage determines the product lifetime.

$$V_{RMS} = \sqrt{V_{AC\ RMS}^2 + V_{DC}^2} \quad (1)$$

or

$$V_{AC\ RMS} = \sqrt{V_{RMS}^2 - V_{DC}^2} \quad (2)$$

where:

V_{RMS} is the total rms working voltage.

$V_{AC\ RMS}$ is the time varying portion of the working voltage.

V_{DC} is the dc offset of the working voltage.

Calculation and Use of Parameters Example

The following example frequently arises in power conversion applications. Assume that the line voltage on one side of the isolation is 240 V_{AC RMS} and a 400 V_{DC} bus voltage is present on the other side of the isolation barrier. The isolator material is polyimide. To establish the critical voltages in determining the creepage, clearance, and lifetime of a device, see Figure 17 and the following equations.

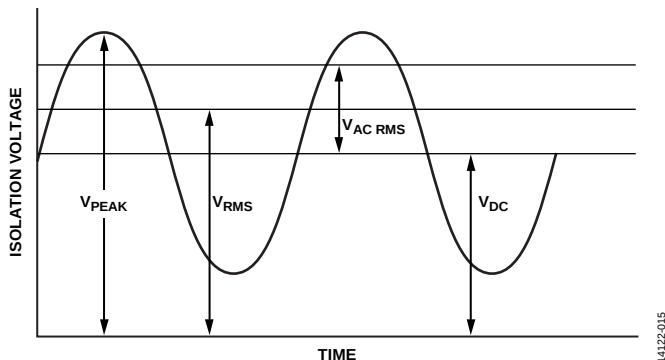


Figure 17. Critical Voltage Example

The working voltage across the barrier from Equation 1 is

$$V_{RMS} = \sqrt{V_{AC\ RMS}^2 + V_{DC}^2}$$

$$V_{RMS} = \sqrt{240^2 + 400^2}$$

$$V_{RMS} = 466\text{ V}$$

This is the working voltage used together with the material group and pollution degree when looking up the creepage required by a system standard.

To determine if the lifetime is adequate, obtain the time varying portion of the working voltage. To obtain the ac rms voltage, use Equation 2.

$$V_{AC\ RMS} = \sqrt{V_{RMS}^2 - V_{DC}^2}$$

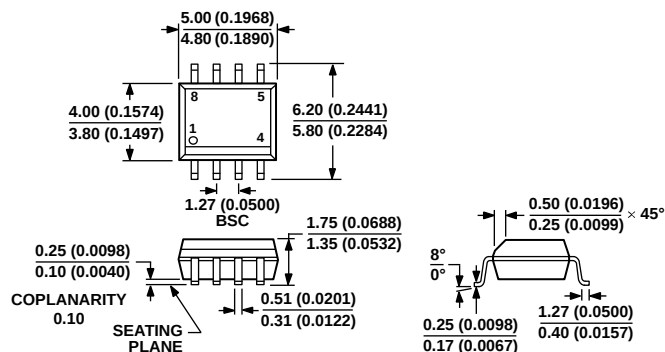
$$V_{AC\ RMS} = \sqrt{466^2 - 400^2}$$

$$V_{AC\ RMS} = 240\text{ V rms}$$

In this case, the ac rms voltage is simply the line voltage of 240 V rms. This calculation is more relevant when the waveform is not sinusoidal. The value is compared to the limits for working voltage in Table 15 for the expected lifetime, less than a 60 Hz sine wave, and it is well within the limit for a 50-year service life.

Note that the dc working voltage limit in Table 15 is set by the creepage of the package as specified in IEC 60664-1. This value can differ for specific system level standards.

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-012-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

02407-A

Figure 18. 8-Lead Standard Small Outline Package [SOIC_N]
Narrow Body (R-8)

Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model ^{1, 2}	Temperature Range	No. of Inputs, V _{DD1} Side	No. of Inputs, V _{DD2} Side	Withstand Voltage Rating (kV rms)	Fail-Safe Output State	Package Description	Package Option
ADuM120N1BRZ	−40°C to +125°C	2	0	3	High	8-Lead SOIC_N	R-8
ADuM120N1BRZ-RL7	−40°C to +125°C	2	0	3	High	8-Lead SOIC_N, Tape and Reel	R-8
ADuM120N0BRZ	−40°C to +125°C	2	0	3	Low	8-Lead SOIC_N	R-8
ADuM120N0BRZ-RL7	−40°C to +125°C	2	0	3	Low	8-Lead SOIC_N, Tape and Reel	R-8
ADuM120N1WBRZ	−40°C to +125°C	2	0	3	High	8-Lead SOIC_N	R-8
ADuM120N1WBRZ-RL7	−40°C to +125°C	2	0	3	High	8-Lead SOIC_N, Tape and Reel	R-8
ADuM120N0WBRZ	−40°C to +125°C	2	0	3	Low	8-Lead SOIC_N	R-8
ADuM120N0WBRZ-RL7	−40°C to +125°C	2	0	3	Low	8-Lead SOIC_N, Tape and Reel	R-8
ADuM121N1BRZ	−40°C to +125°C	1	1	3	High	8-Lead SOIC_N	R-8
ADuM121N1BRZ-RL7	−40°C to +125°C	1	1	3	High	8-Lead SOIC_N, Tape and Reel	R-8
ADuM121N0BRZ	−40°C to +125°C	1	1	3	Low	8-Lead SOIC_N	R-8
ADuM121N0BRZ-RL7	−40°C to +125°C	1	1	3	Low	8-Lead SOIC_N, Tape and Reel	R-8
ADuM121N1WBRZ	−40°C to +125°C	1	1	3	High	8-Lead SOIC_N	R-8
ADuM121N1WBRZ-RL7	−40°C to +125°C	1	1	3	High	8-Lead SOIC_N, Tape and Reel	R-8
ADuM121N0WBRZ	−40°C to +125°C	1	1	3	Low	8-Lead SOIC_N	R-8
ADuM121N0WBRZ-RL7	−40°C to +125°C	1	1	3	Low	8-Lead SOIC_N, Tape and Reel	R-8

¹ Z = RoHS Compliant Part.

² W = Qualified for Automotive Applications.

AUTOMOTIVE PRODUCTS

The ADuM121N1WBRZ and the ADuM121N1WBRZ-RL7 models are available with controlled manufacturing to support the quality and reliability requirements of automotive applications. Note that these automotive models may have specifications that differ from the commercial models; therefore, designers should review the Specifications section of this data sheet carefully. Only the automotive grade products shown are available for use in automotive applications. Contact your local Analog Devices account representative for specific product ordering information and to obtain the specific Automotive Reliability reports for these models.